

STARPOWER

SEMICONDUCTOR™

IGBT

GD600HFT120P1S

Molding Type Module**1200V/600A 2 in one-package**

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as wind and solar power.



Features

- Low $V_{CE(sat)}$ trench IGBT technology
- 10 μ s short circuit capability
- Low inductance case
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- High power and thermal cycling capability

Typical Applications

- Auxiliary Inverters
- High Power Converters
- UPS
- Wind and Solar Power
- Traction Drivers

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Description	GD600HFT120P1S	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=100^{\circ}\text{C}$	1000 600	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1200	A
I_F	Diode Continuous Forward Current @ $T_C=100^{\circ}\text{C}$	600	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1200	A
P_D	Maximum Power Dissipation @ $T_J=175^{\circ}\text{C}$	3386	W
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V
Mounting Torque	Power Terminal Screw:M4	1.8 to 2.1	N.m
	Power Terminal Screw:M8	8.0 to 10	
	Mounting Screw:M5	3.0 to 5.0	N.m

Electrical Characteristics of IGBT $T_C=25^{\circ}\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_J=25^{\circ}\text{C}$	1200			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}$, $V_{GE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=24.0\text{mA}$, $V_{CE}=V_{GE}$, $T_J=25^{\circ}\text{C}$	5.2	5.8	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=600\text{A}$, $V_{GE}=15\text{V}$, $T_J=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=600\text{A}$, $V_{GE}=15\text{V}$, $T_J=125^{\circ}\text{C}$		2.00		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=600A,$ $R_G=1.6\Omega, V_{GE}=\pm 15V,$ $T_j=25^\circ C$		260		ns
t_r	Rise Time			100		ns
$t_{d(off)}$	Turn-Off Delay Time			560		ns
t_f	Fall Time			140		ns
E_{on}	Turn-On Switching Loss			/		mJ
E_{off}	Turn-Off Switching Loss			/		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=600A,$ $R_G=1.6\Omega, V_{GE}=\pm 15V,$ $T_j=125^\circ C$		310		ns
t_r	Rise Time			110		ns
$t_{d(off)}$	Turn-Off Delay Time			660		ns
t_f	Fall Time			190		ns
E_{on}	Turn-On Switching Loss			45.0		mJ
E_{off}	Turn-Off Switching Loss			105		mJ
C_{ies}	Input Capacitance	$V_{CE}=25V, f=1MHz,$ $V_{GE}=0V$		43.3		nF
C_{oes}	Output Capacitance			2.26		nF
C_{res}	Reverse Transfer Capacitance			1.96		nF
I_{SC}	SC Data	$t_p \leq 10\mu s, V_{GE}=15V,$ $T_j=125^\circ C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$		2400		A
R_{Gint}	Internal Gate Resistance			1.7		Ω
L_{CE}	Stray Inductance			18		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip			0.30		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=600A$	$T_j=25^\circ C$	1.65	2.15	V
			$T_j=125^\circ C$	1.65		
Q_r	Recovered Charge	$I_F=600A,$ $V_R=600V,$ $R_G=1.6\Omega,$ $V_{GE}=-15V$	$T_j=25^\circ C$	60		μC
			$T_j=125^\circ C$	108		
I_{RM}	Peak Reverse Recovery Current		$T_j=25^\circ C$	225		A
			$T_j=125^\circ C$	285		
E_{rec}	Reverse Recovery Energy		$T_j=25^\circ C$	27.0		mJ
			$T_j=125^\circ C$	51.0		

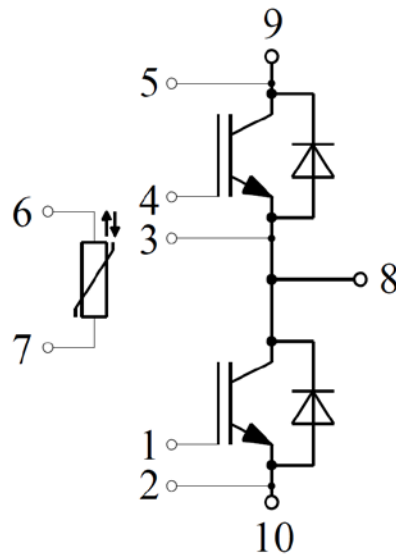
Electrical Characteristics of NTC $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Thermal Characteristics

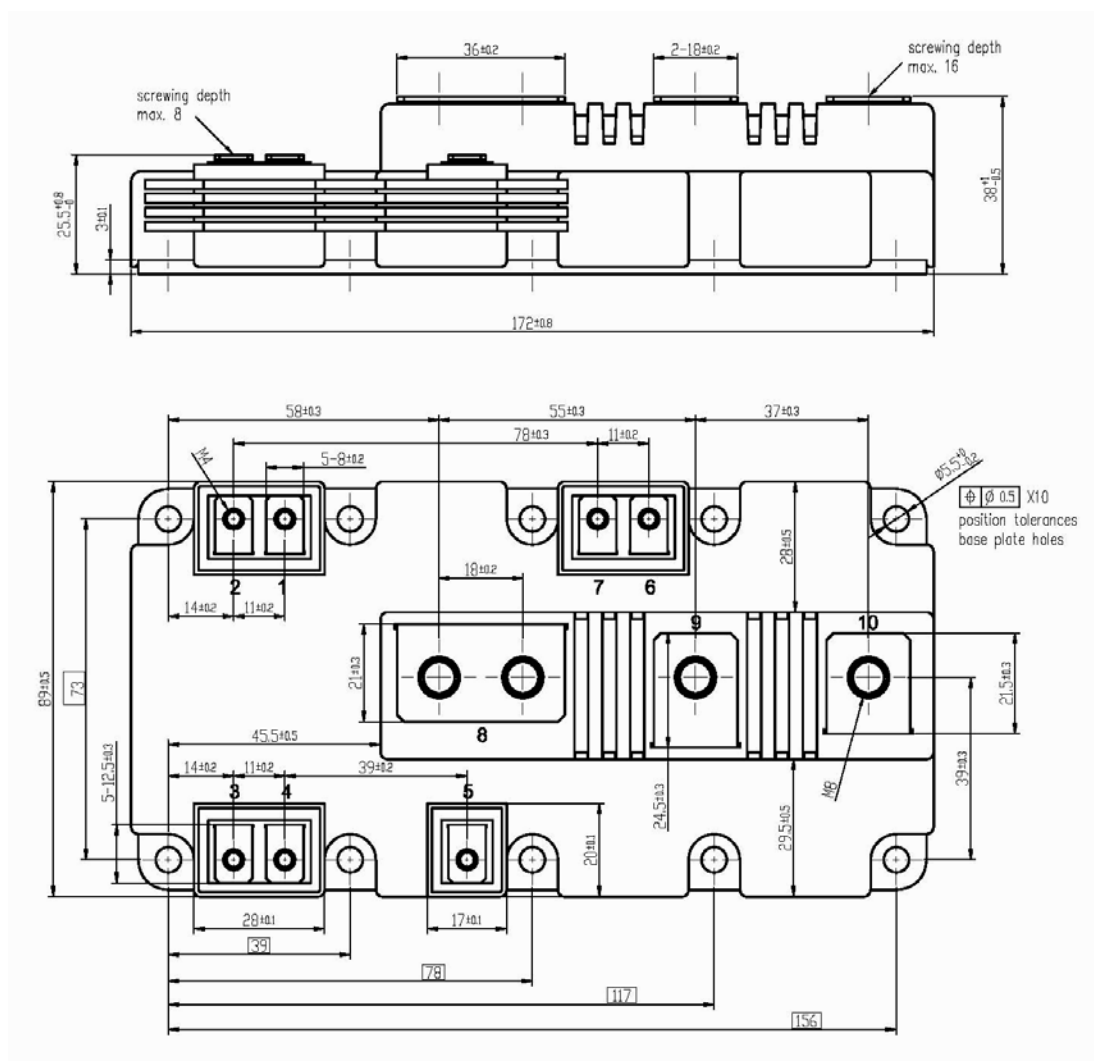
Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per IGBT)		44.3	K/kW
$R_{\theta JC}$	Junction-to-Case (per DIODE)		78.9	K/kW
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	4.5		K/kW
Weight	Weight of Module	825		g

Equivalent Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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